List of reference symbols

| 1, SUB | semiconductor substrate |
|-----------|--|
| K | channel region |
| S, 200 | first doping region |
| D, 300 | second doping region |
| D1 | first gate dielectric |
| d | thickness of D1 |
| D2 | second gate dielectric |
| ď' | thickness of D2 |
| GL | gate conductor |
| 2, 3 | p-type wells of the selection transistor |
| 4 | n-type channel region of the selection |
| | transistor |
| 50 | gate dielectric of the selection |
| | transistor |
| 30 | gate stack of the selection transistor |
| 5 | trench of the trench capacitor |
| 100 | trench capacitor dielectric |
| 15 | filling electrode |
| 20, 20' | insulation collar |
| 18 | buried connection |
| 19 | insulation cover |
| 145, 145' | first gate dielectric |
| 150 | second gate dielectric |
| 155 | third gate dielectric |
| 101 | n-type buried plate |